

TOSHIBA TRANSISTOR SILICON PNP TRIPLE DIFFUSED (PCT PROCESS)

2SA1255

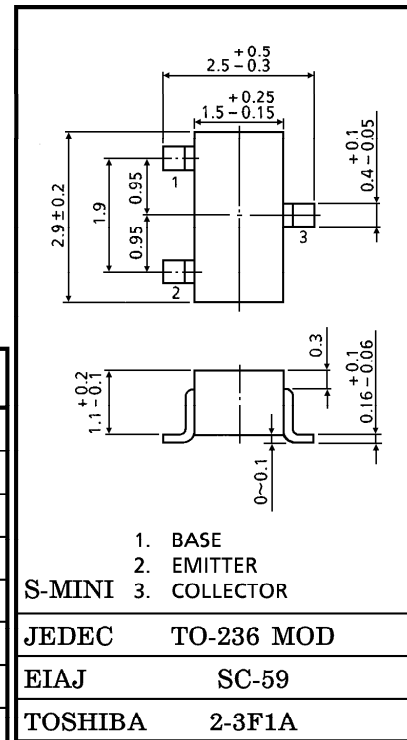
HIGH VOLTAGE SWITCHING APPLICATIONS

Unit in mm

- High Voltage : $V_{CBO} = -200V$ (Min.)
 $V_{CEO} = -200V$ (Min.)
- Small Package
- Complementary to 2SC3138

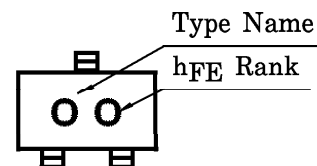
MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-200	V
Collector-Emitter Voltage	V_{CEO}	-200	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-50	mA
Base Current	I_B	-20	mA
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_j	125	$^\circ C$
Storage Temperature Range	T_{stg}	-55~125	$^\circ C$



Weight : 0.012g

Marking



961001EAA2

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -200V, I_E = 0$	—	—	-0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$	—	—	-0.1	μA
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -0.1mA, I_E = 0$	-200	—	—	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-200	—	—	V
DC Current Gain	h_{FE} (Note)	$V_{CE} = -3V, I_C = -10mA$	70	—	240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -10mA, I_B = -1mA$	—	-0.2	-1	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -10mA, I_B = -1mA$	—	-0.75	-1.5	V
Transition Frequency	f_T	$V_{CE} = -10V, I_C = -2mA$	50	100	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	—	3	7	pF
Switching Time	Turn-on Time	$V_{CC} = -50V, I_C = -6mA$ $-I_{B1} = I_{B2} = 0.6mA$ PULSE WIDTH = $5\mu s$ DUTY CYCLE $\leq 2\%$	—	0.3	—	μs
	Storage Time		—	2	—	μs
	Fall Time		—	0.4	—	μs

Note : h_{FE} Classification O : 70~140, Y : 120~240

